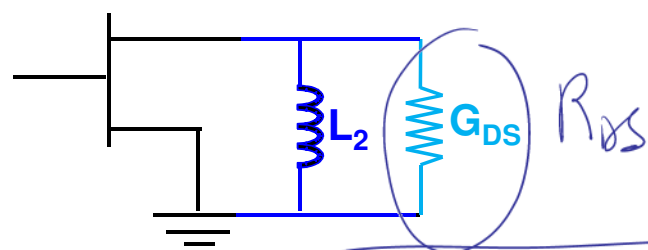
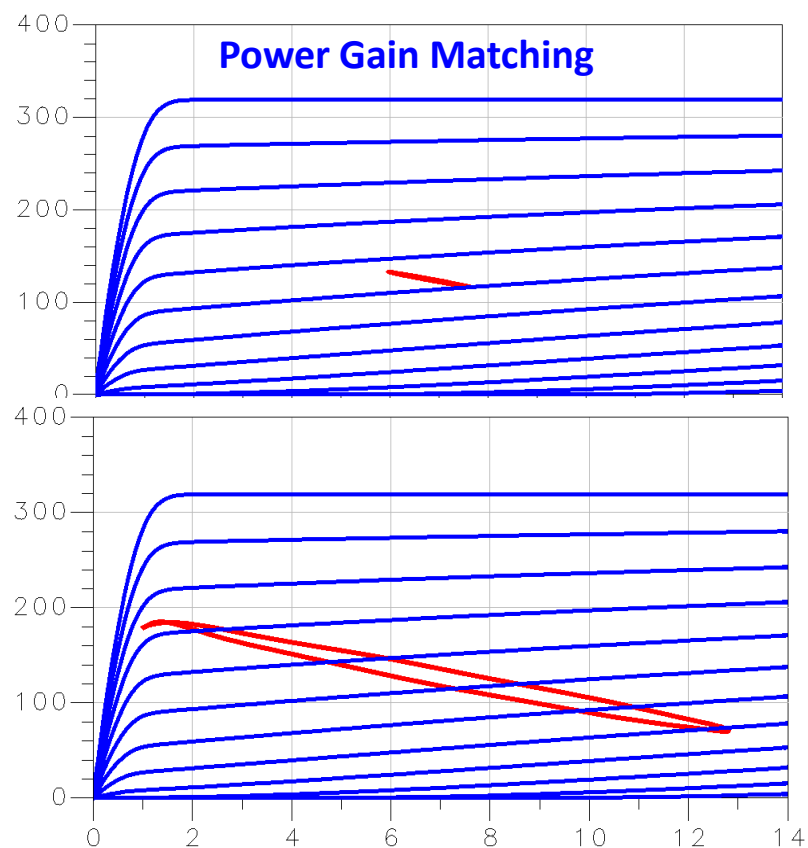
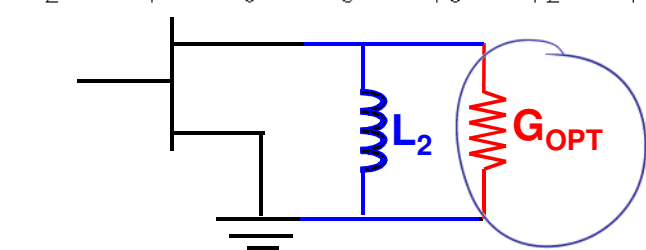
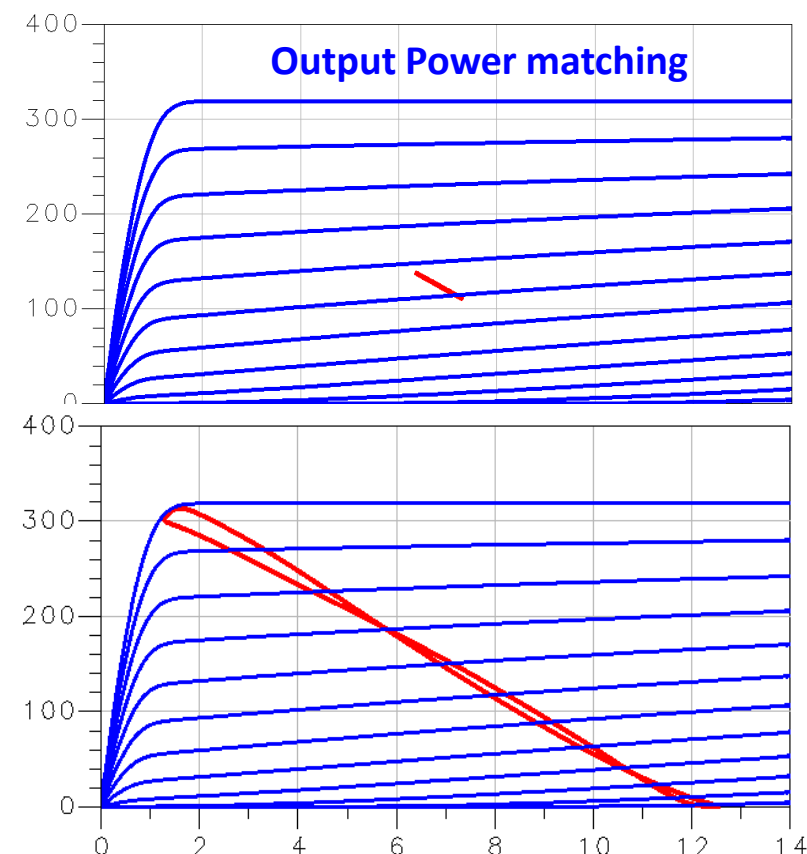


Matching principles of narrow-band amplifiers At high frequencies



$$G_{max} \cdot P_{out}(R_{DS}) = \frac{R_{opt}}{R_{DS}} P_{out,MAX}$$

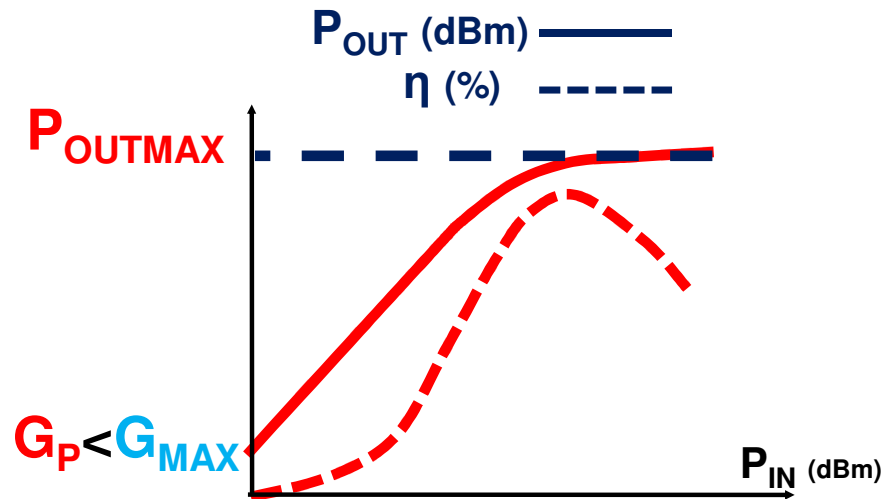
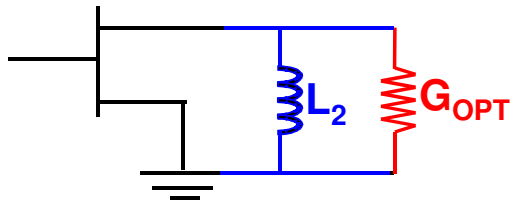
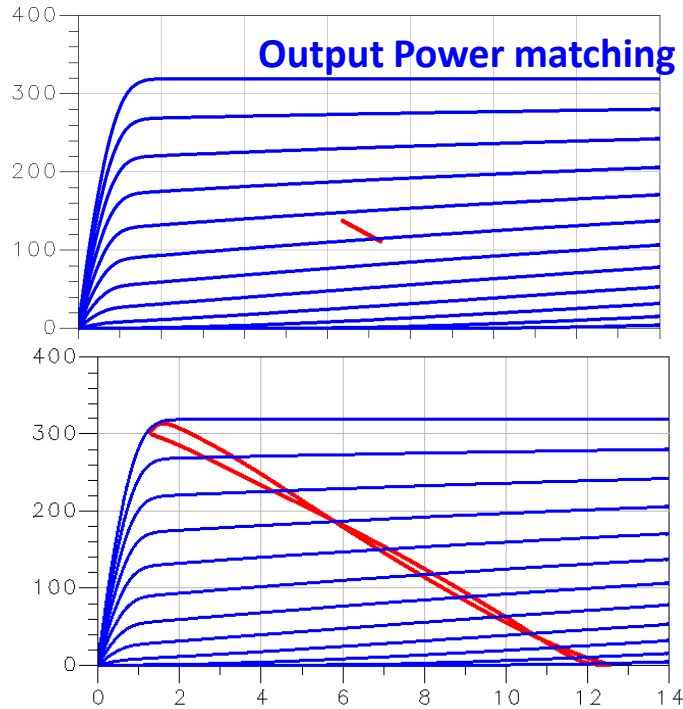


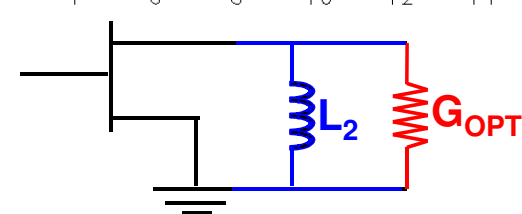
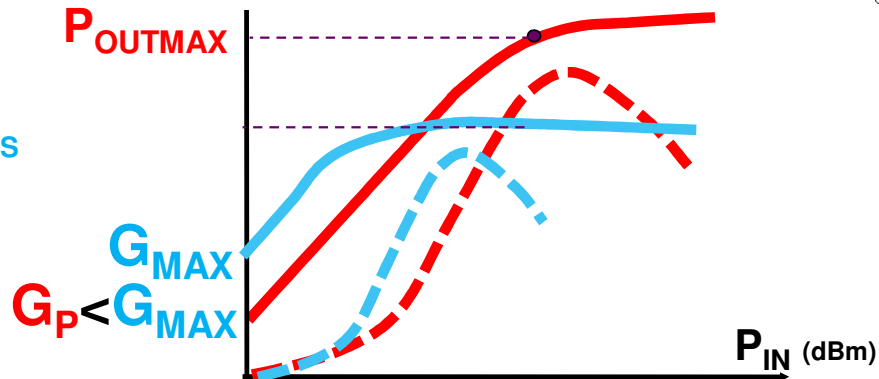
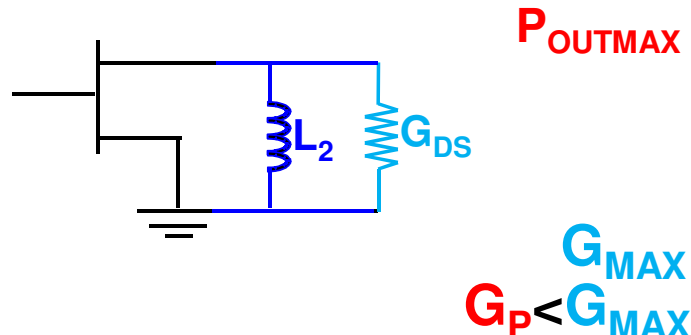
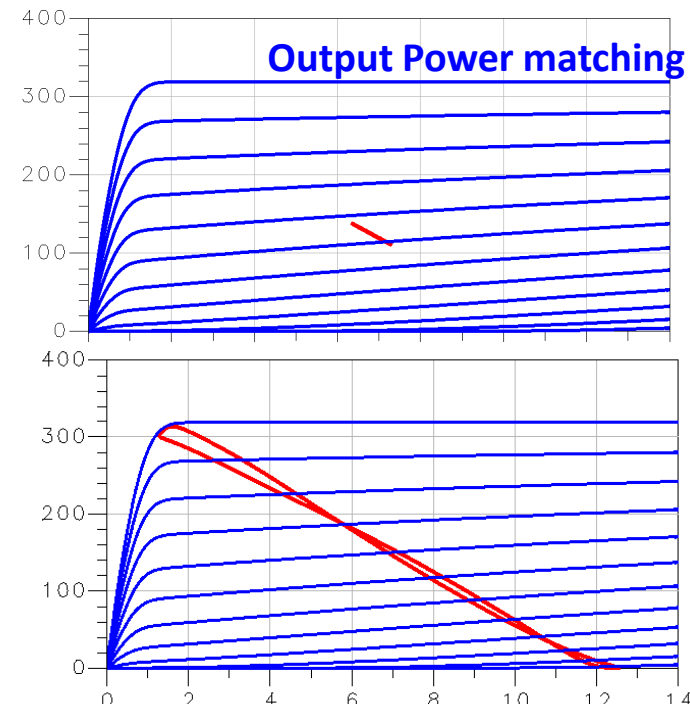
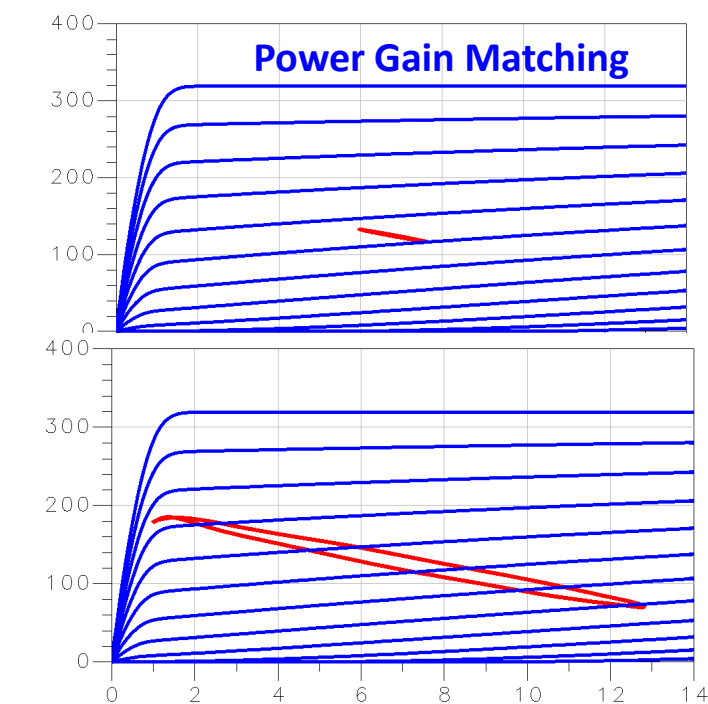
$$G_p < G_{max} \cdot R_{opt}$$

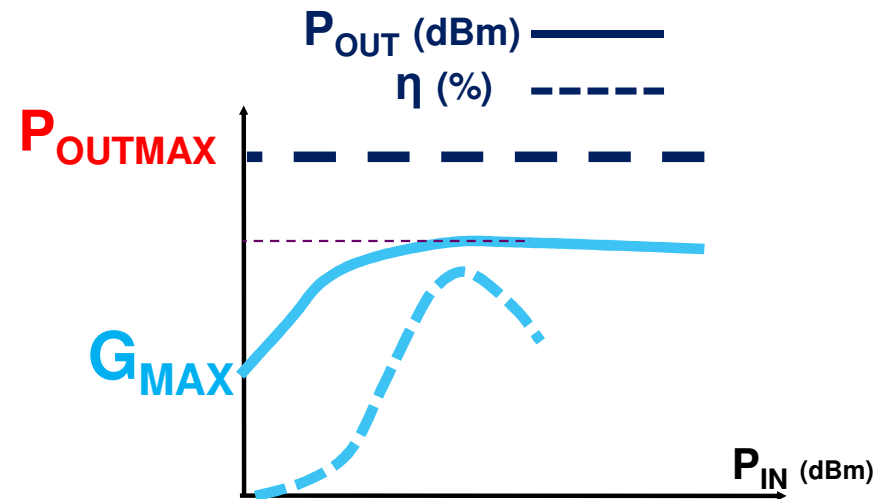
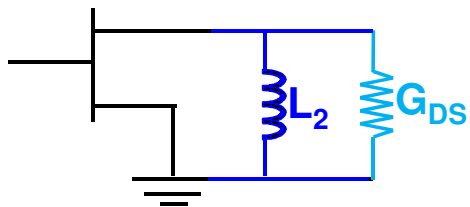
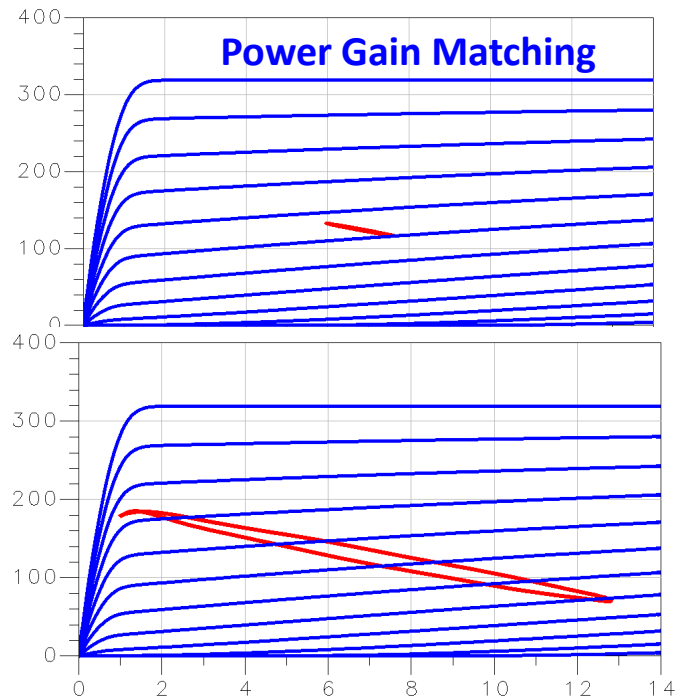
$$P_{OUT}(R_{DS}) = \frac{1}{2} \frac{\left[\frac{1}{2} (V_{DSMAX} - V_{DSMIN})^2 \right]}{R_{DS}} \longleftrightarrow P_{OUT}(R_{OPT}) = \frac{1}{2} \frac{\left[\frac{1}{2} (V_{DSMAX} - V_{DSMIN})^2 \right]^2}{R_{OPT}}$$

EMIMEO

E(rasmus) Mundus on Innovative Microwave Electronics and Optics

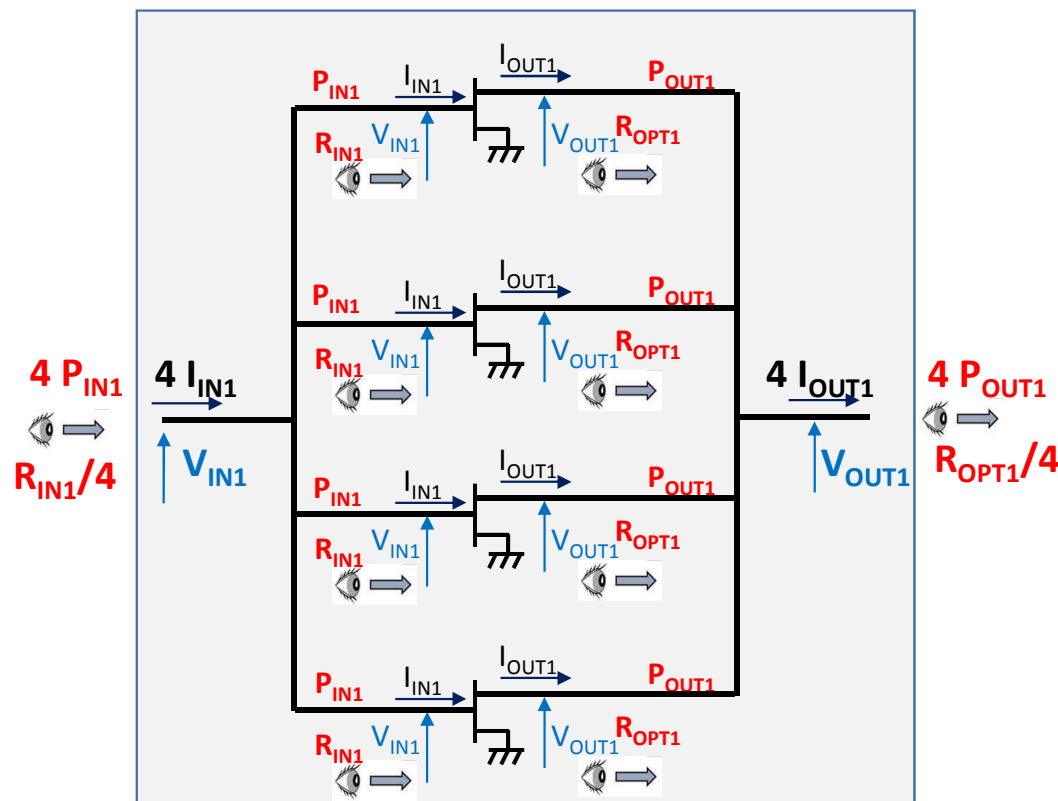
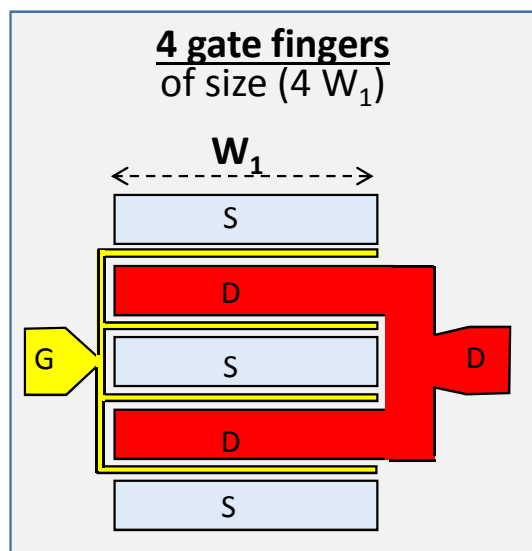






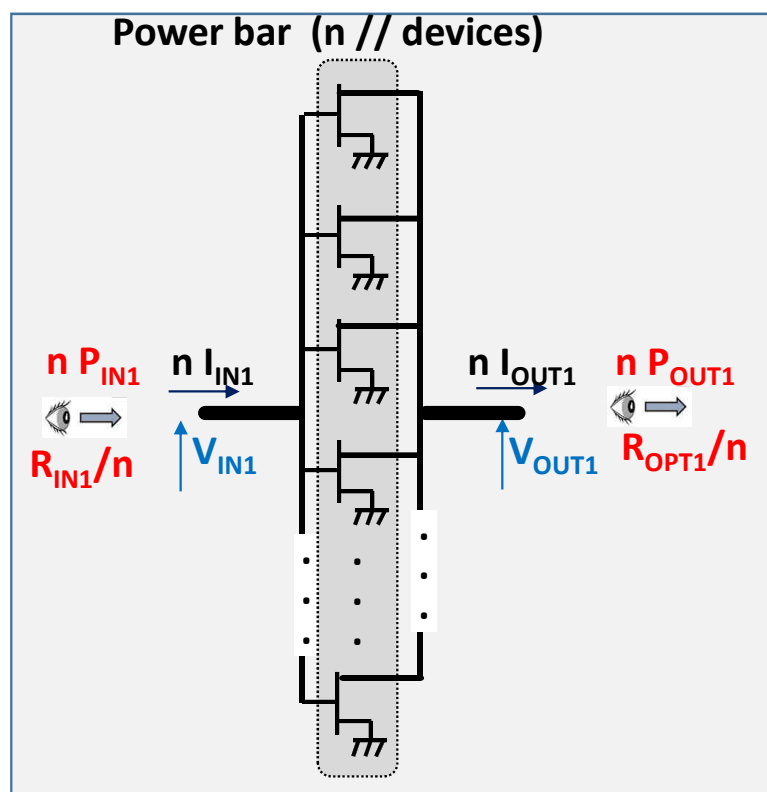
Power combination (Power Bars) and power matching

■ Illustration of critical issues in power matching

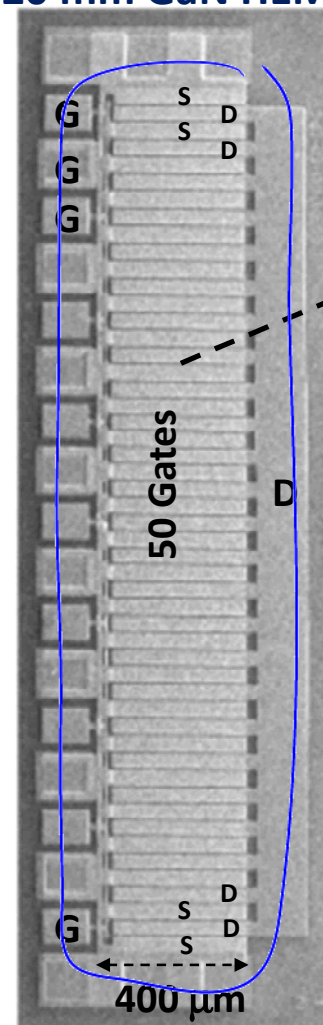


Power combination (Power Bars) and power matching

■ Illustration of critical issues in power matching



20 mm GaN HEMT die

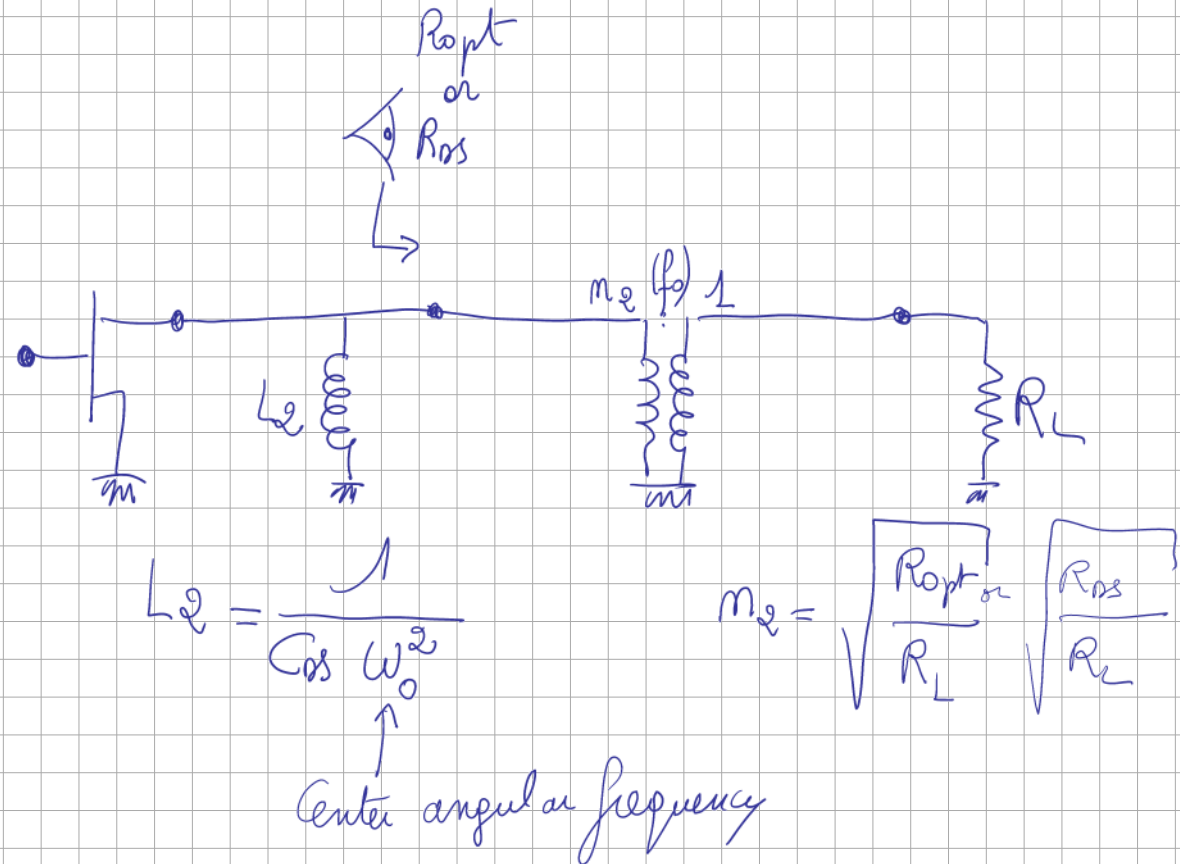
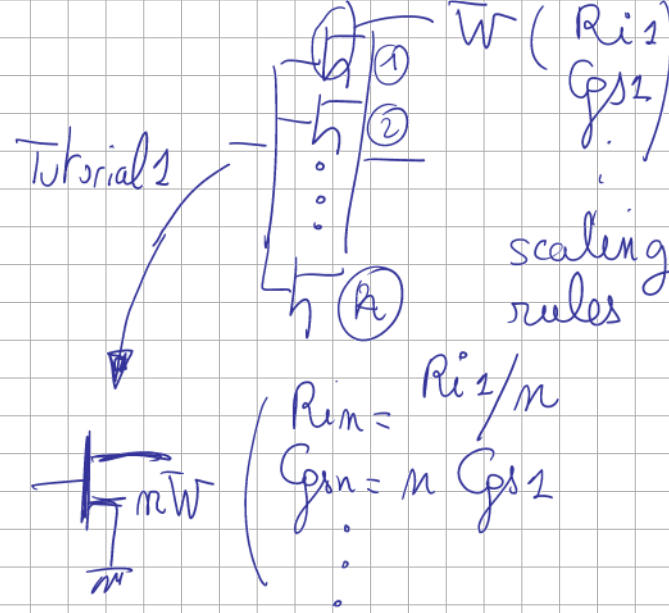


■ Device Size

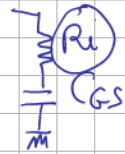
$$\begin{aligned}
 &= \text{Total Gate Width} \\
 &= (\text{N}^\circ \text{ of // gates}) \times (\text{Gate width}) \\
 &= 50 \times 400 \mu\text{m} = \mathbf{20 \text{ mm}}
 \end{aligned}$$

■ Scaling Rules:

- Drain Current
 $I_{DS} \text{ (mA/mm)}$
- Voltages
 $V_{GS} \text{ and } V_{DS} \text{ (V)}$
- Output Power
 $P_{OUT} \text{ (W/mm)}$
- Optimum Output Load
 $R_{OPT} \text{ (}\Omega \cdot \text{mm)}$



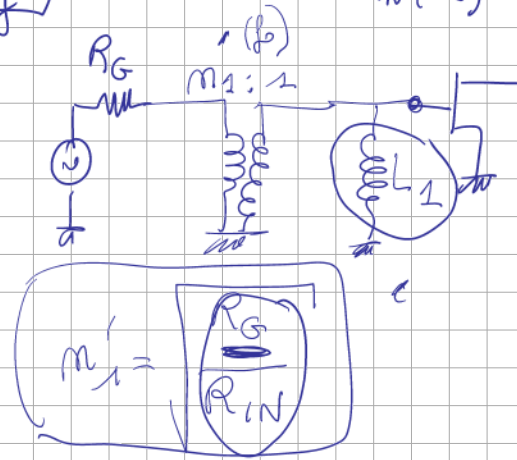
R_i C_{gs} in series



INPUT matching

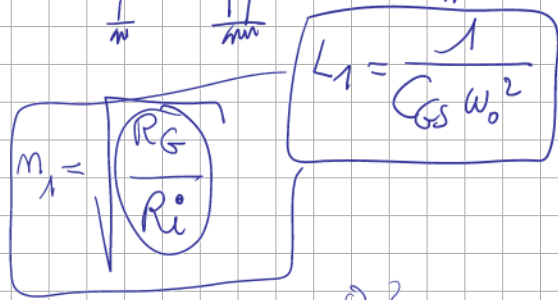
OR

$R_{IN}(\omega_0)$ C_{gs} in //



$$R_{IN}(\omega_0) = \frac{1}{R_i C_{gs}^2 \omega_0^2}$$

$$n = \frac{1}{m}$$



$$L_1 = \frac{1}{C_{gs} \omega_0^2}$$

$$m_1 = \sqrt{\frac{R_G}{R_i}}$$

0.3

0.35

$$n = 1$$

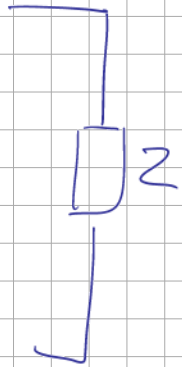
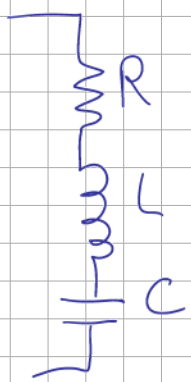
$$m_1 = 0.7$$

$$\frac{1}{0.7} \approx 1.4$$

$$Q_{IN} =$$

$$m'_1 = 1.35$$

RLC series resonant circuit



$$Z = R + j \left(L\omega - \frac{1}{C\omega} \right)$$

$$\text{Imag}(Z)_{(\omega_0)} = 0$$

$$\omega_0 = \frac{1}{\sqrt{LC}}$$

$$f_0 = \frac{1}{2\pi\sqrt{LC}}$$

$$Z = R \left[1 + j \frac{1}{R} \left(L\omega - \frac{1}{C\omega} \right) \right]$$

$$= R \left[1 + j \frac{L\omega}{R} \left(1 - \frac{1}{LC\omega^2} \right) \right]$$

$$Q_S = \frac{L\omega_0}{R} = \frac{1}{RC\omega_0}$$

Quality factor Q_S of resonant circuit

$$= R \left[1 + j \frac{L\omega_0}{R} \left(\frac{\omega}{\omega_0} - \frac{\omega_0}{\omega} \right) \right]$$

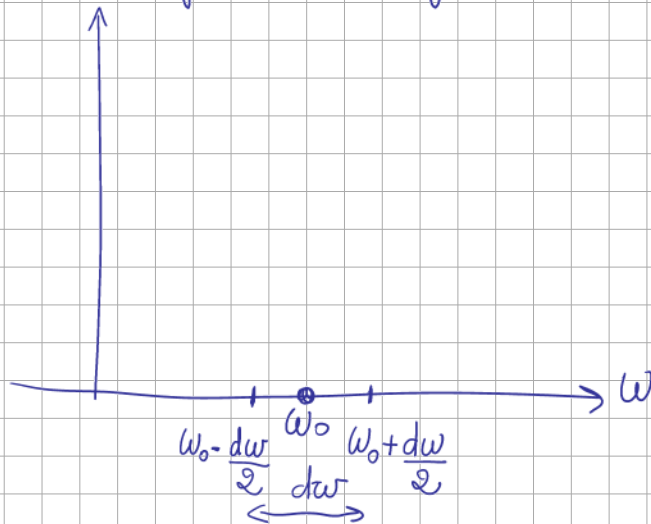
$$Z = R \left[1 + j Q_S \left(\frac{\omega}{\omega_0} - \frac{\omega_0}{\omega} \right) \right] \quad \text{because } LC = \frac{1}{\omega_0^2}$$

$$\lim_{\omega \rightarrow \omega_0} Z_S = \lim_{\omega \rightarrow \omega_0} R \left[1 + j Q_S \frac{\omega^2 - \omega_0^2}{\omega \omega_0} \right]$$

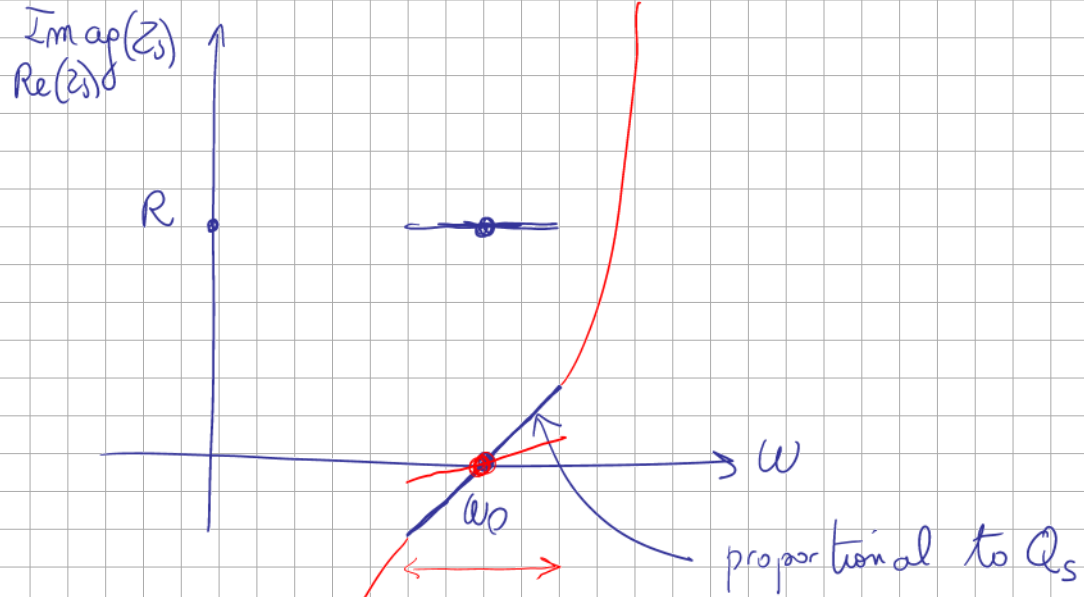
$$\omega = \omega_0 + \frac{d\omega}{2} \quad \text{where } d\omega \ll \omega_0$$

$$= \lim_{\omega \rightarrow \omega_0} R \left[1 + j Q_S \frac{(\omega + \omega_0)(\omega - \omega_0)}{\omega \omega_0} \right]$$

Handwritten notes: $2\omega_0 + \frac{d\omega}{2} \approx 2\omega_0$, $\frac{d\omega}{2}$, and ω_0^2 circled.



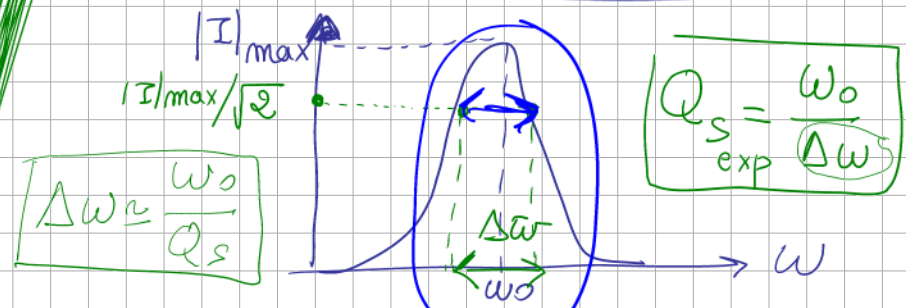
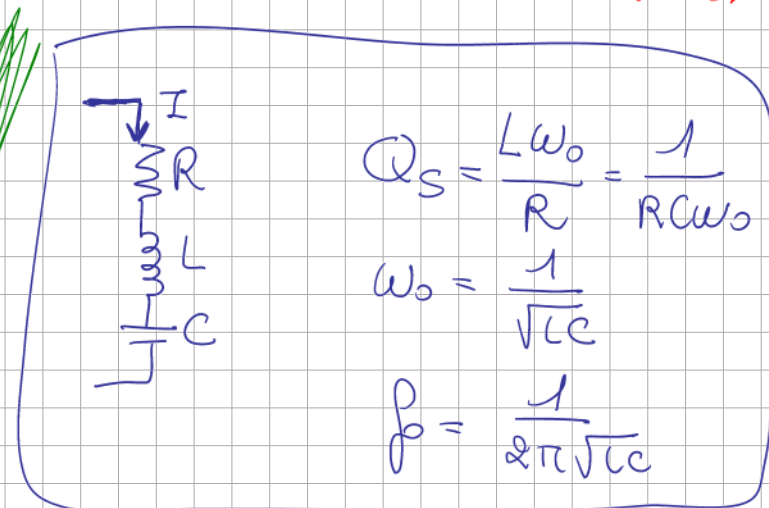
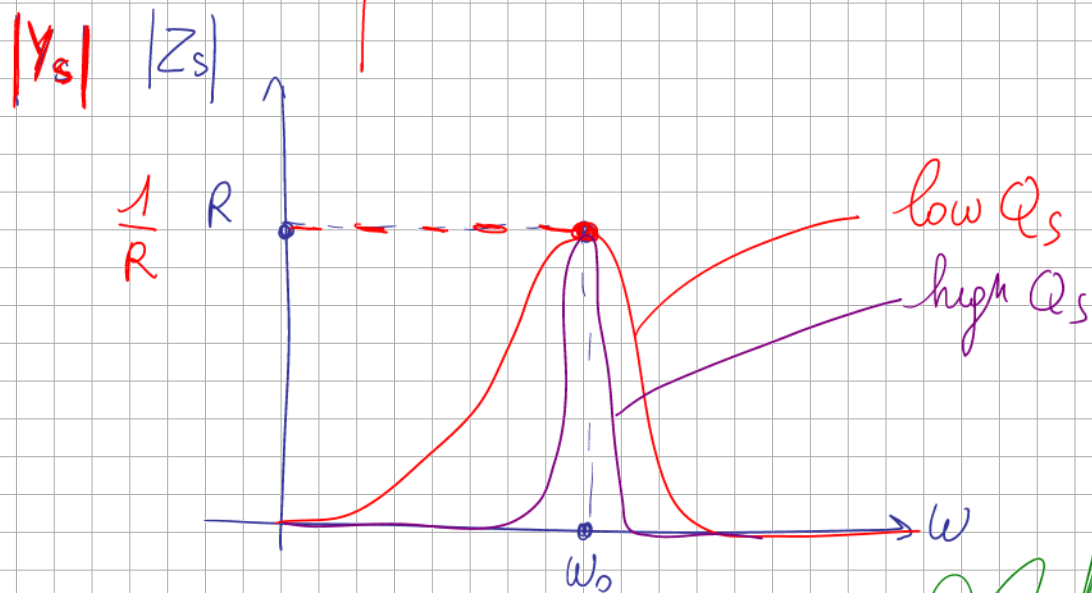
$$\lim_{\omega \rightarrow \omega_0} Z_S = R \left[1 + j \left(\frac{Q_S}{\omega_0} \right) d\omega \right]$$



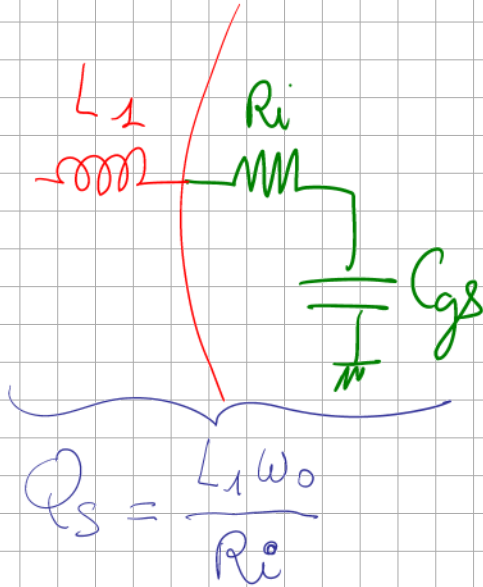
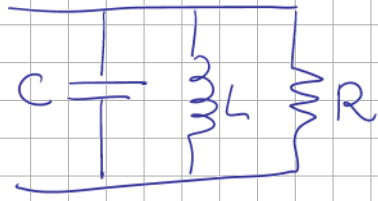
$$\begin{cases} Q_s = \frac{L\omega_0}{R} = \frac{1}{RC\omega_0} \\ \frac{Q_s}{\omega_0} = \frac{L}{R} \end{cases}$$

if $Q_s \gg 1 \Rightarrow$ highly resonant
 \Rightarrow Bandwidth \ll

if $Q_s \ll 1 \Rightarrow$ low resonant factor
 \Rightarrow Bandwidth \gg

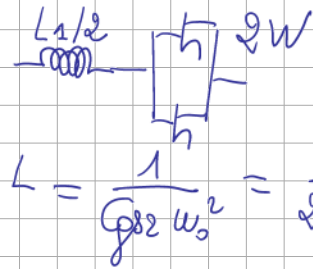


$$Y_P \approx \left(\frac{1}{R} \right) \left[1 + j Q_P \left(\frac{\omega}{\omega_0} - \frac{\omega_0}{\omega} \right) \right]$$



$$L_1 = \frac{1}{C_{gs2} \omega_0^2}$$

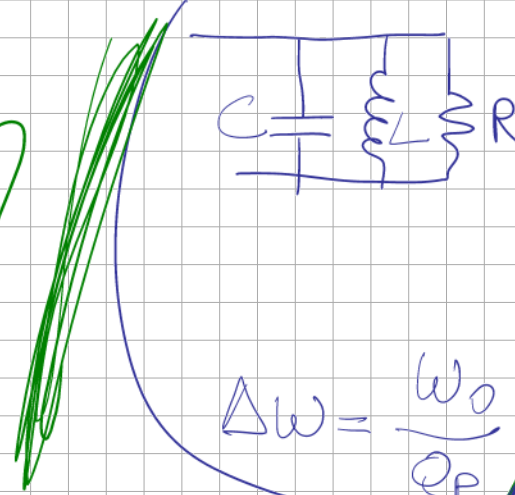
$$Q_S = \frac{L_1 \omega_0}{R_{i1}}$$



$$L = \frac{1}{C_{gs2}^2 \omega_0^2} = \frac{1}{2 C_{gs1} \omega_0^2} = \frac{L_1}{2}$$

$$Q'_S = \frac{L \omega_0}{R_{i2}} = \frac{(L_1/2) \omega_0}{\left(\frac{R_{i1}}{2} \right)} = \frac{L_1 \omega_0}{R_{i1}}$$

$= Q_S$ (does not depend on transistor size)

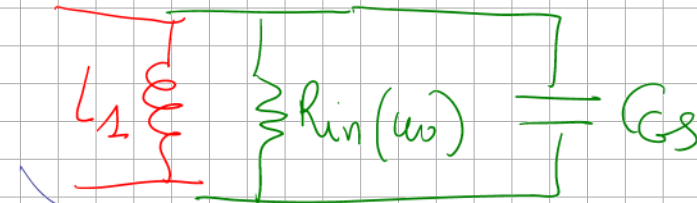


$$Q_P = \frac{R}{L \omega_0} = R C \omega_0$$

$$\omega_0 = \frac{1}{\sqrt{LC}}$$

$$\beta = \frac{1}{2\pi \sqrt{LC}}$$

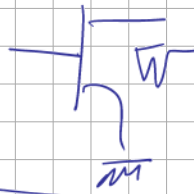
$$\Delta \omega = \frac{\omega_0}{Q_P}$$



$$Q_P = \frac{R_{in}}{L_1 \omega_0} = \frac{(1/[R_i C_{gs}^2 \omega_0^2])}{L_1 \omega_0} = \frac{1}{C_{gs} \omega_0^2}$$

$$= \frac{1}{R_i C_{gs} \omega_0^2} \cdot \frac{1}{C_{gs} \omega_0^2} \omega_0$$

$$= \frac{1}{R_i C_{gs} \omega_0} = \frac{L_1 \omega_0}{R_i}$$



$$Q_{IN} = \frac{L_1 \omega_0}{R_i} = \frac{1}{R_i C_{gs} \omega_0}$$

$$Q_{IN}(\omega_0) = \frac{1}{R_i C_{gs} \omega_0}$$

$$\Delta \omega \leq \frac{\omega_0}{Q_{IN}(\omega_0)}$$

$$Q_{IN} = 10$$

2^m devices placed in parallel

- 1
- 2
- 4
- 8
- 16



$$R_{DS} \parallel C_{DS} \parallel L_2 = \frac{1}{C_{DS} \omega_0^2}$$

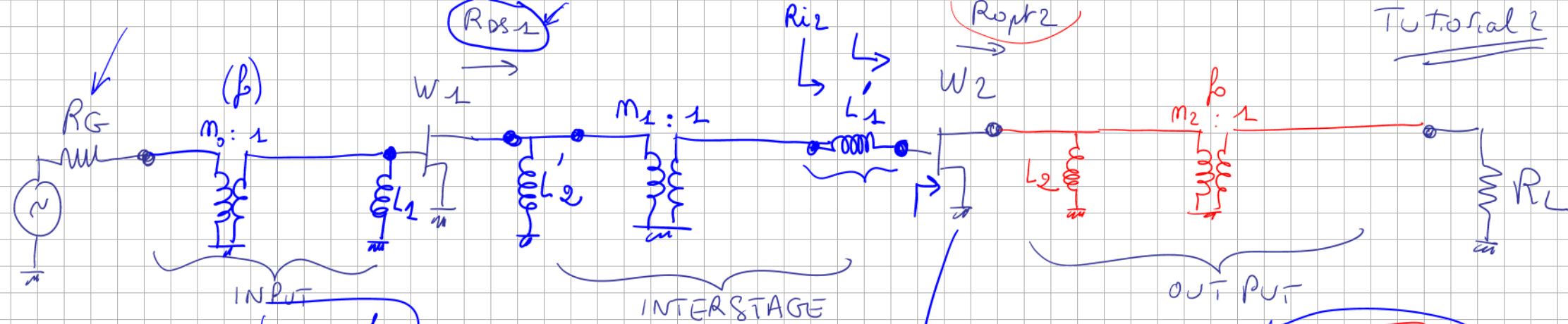
$$Q_{OUT} = \frac{R_{DS}}{L_2 \omega_0} = R_{DS} C_{DS} \omega_0$$

$$Q_{OUT}(\omega_0) = R_{DS} C_{DS} \omega_0$$

$$\Delta \omega \leq \frac{\omega_0}{Q_{OUT}(\omega_0)}$$

$$Q_{OUT} = 5$$





$$R_{IN1} = \frac{1}{R_{L1} G_{S1}^2 \omega_0^2}$$

R_{L1}

$$\frac{R_G}{R_{L1}}$$

$$\frac{R_{IN1}}{R_G}$$

Chosen

$$L_1 = \frac{1}{G_{S1} \omega_0^2}$$

$$m_0 = \sqrt{\frac{R_G}{R_{IN1}}}$$

$$L'_1 = \frac{1}{G_{S2} \omega_0^2}$$

$$L'_2 = \frac{1}{G_{S2} \omega_0^2}$$

$$m_1 = \sqrt{\frac{R_{DS1}}{R_{L2}}}$$

$$L_2 = \frac{1}{G_{S2} \omega_0^2}$$

$$R_{IN2} = \frac{1}{R_{L2} G_{S2}^2 \omega_0^2}$$

$\frac{R_{DS1}}{R_{L2}}$ and $\frac{R_{DS1}}{R_{IN2}}$?

$$m_2 = \sqrt{\frac{R_{opt2}}{R_L}}$$

R_{IN}